

2SC1623

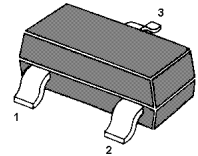
NPN TRANSISTOR

FEATURE

High DC current gain : $h_{FE}=200(\text{Typ})$ $V_{CE}=6\text{V}$, $I_C=1\text{mA}$

High voltage: $V_{CEO}=50\text{V}$

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1. BASE
2. EMITTER
3. COLLECTOR

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

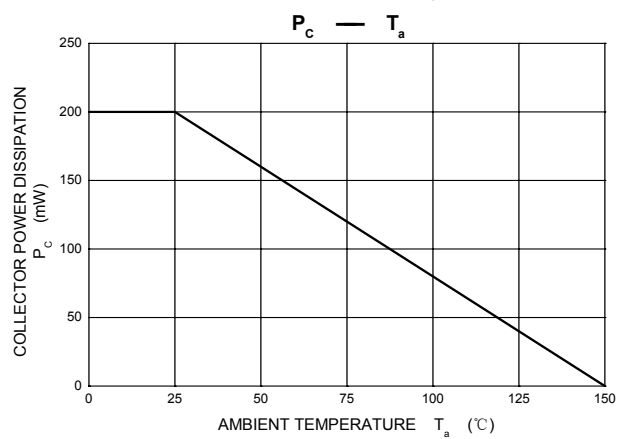
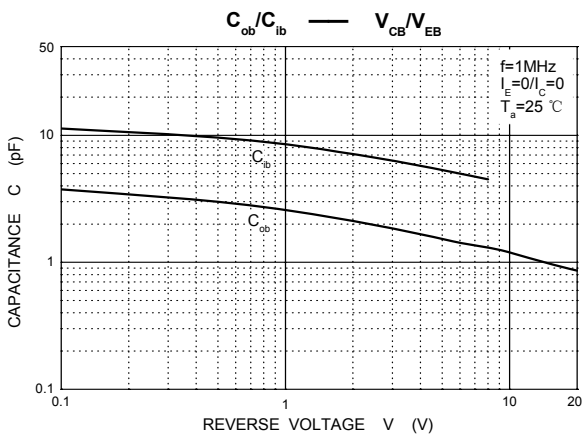
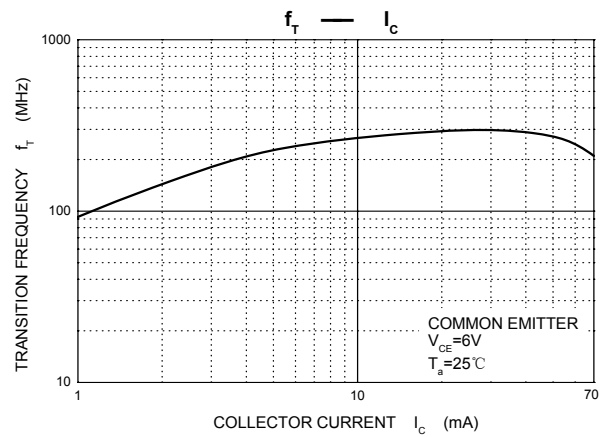
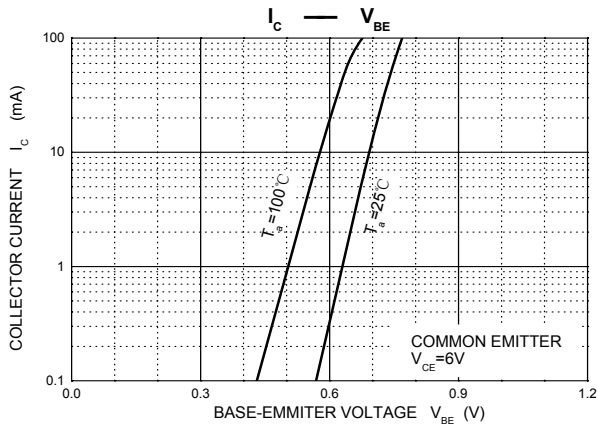
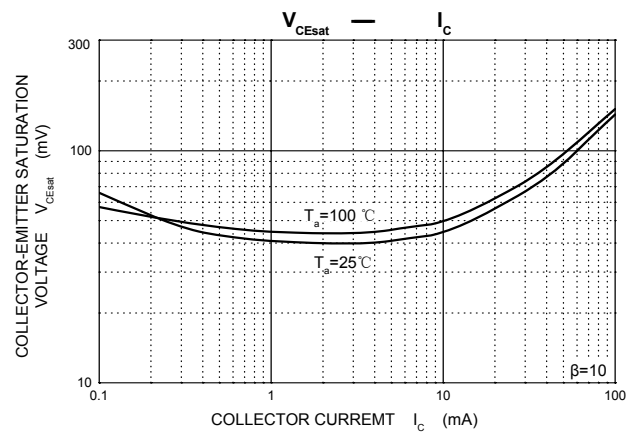
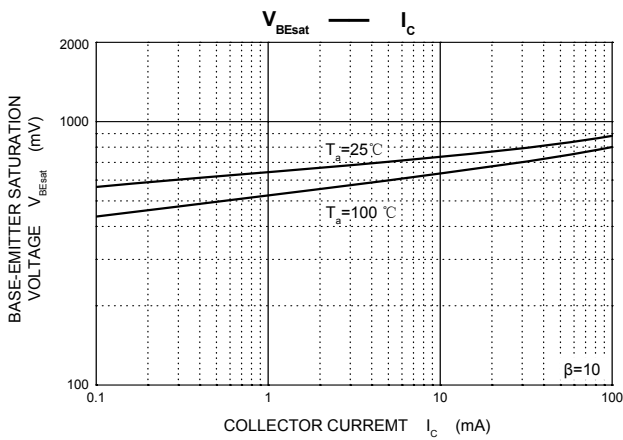
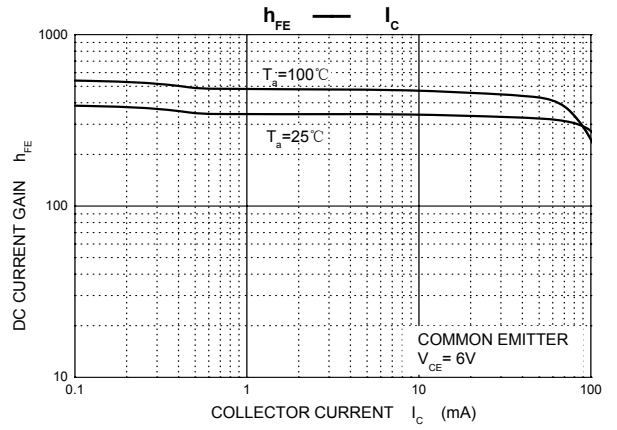
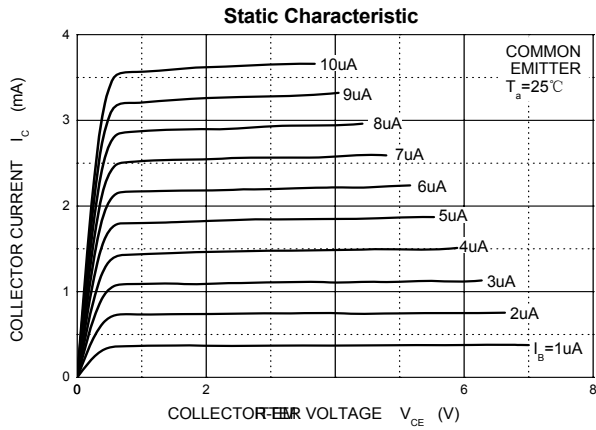
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	100	mA
P_C	Collector Power Dissipation	200	mW
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

MARKING: L6

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test condition	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}$, $I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}$, $I_C=1\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=6\text{V}$, $I_C=10\text{mA}$		250		MHz

Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

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